

**Claim Amendments:**

This listing of claims will replace all prior versions, and listings, of claims in the application:

1. (Currently Amended) A method of forming a superconductive device, comprising:  
cleaning a substrate having a dimension ratio of not less than about  $10^2$ , the cleaning  
including immersing the substrate in a fluid medium and subjecting the substrate  
to mechanical waves in the fluid medium;  
plasma treating the substrate; and  
depositing a superconductor layer to overlie the substrate.
2. (Original) The method of claim 1, wherein the fluid medium comprises water.
3. (Original) The method of claim 1, wherein the mechanical waves comprise sound waves.
4. (Original) The method of claim 3, wherein the sound waves are ultrasound waves, having a frequency not less than about 20 kHz.
5. (Original) The method of claim 4, wherein the sound waves have a frequency not less than about 100 kHz.
6. (Original) The method of claim 4, wherein the sound waves have a frequency not less than about 200 kHz.
7. (Original) The method of claim 1, wherein the substrate is translated through the fluid medium in a reel-to-reel process.
8. (Original) The method of claim 7, wherein the substrate is translated continuously through the fluid medium while subjecting the substrate to the mechanical waves.

9. (Currently Amended) The method of claim ~~[[1]]~~8, wherein the substrate is translated through the fluid medium at a rate of at least 2 inches/minute.

10. (Currently Amended) The method of claim ~~[[1]]~~9, wherein the substrate is translated through the fluid medium at a rate of at least 10 inches/minute.

11. (Currently Amended) ~~[[The]]~~A method of forming a superconductive device,

comprising:

~~claim 1, further comprising a step of polishing~~ ~~[[the]]~~a substrate having a dimension ratio not less than  $10^2$ ;

cleaning the substrate, cleaning including immersing the substrate in a fluid medium and  
subjecting the substrate to mechanical waves in the fluid medium;

plasma treating the substrate; and

depositing a superconductor layer to overlie the substrate~~prior to cleaning.~~

12. (Original) The method of claim 11, wherein polishing includes reducing a surface roughness of at least one side of the substrate through a series of successive polishing operations.

13. (Original) The method of claim 11, wherein polishing is carried out by contacting the substrate with an abrasive slurry, and applying a force against the substrate to effect material removal.

14. (Original) The method of claim 1, further comprising a step of executing a high pressure rinse prior to cleaning.

15. (Currently Amended) The method of claim 1, further comprising exposing the substrate to an annealing step after cleaning and prior to depositing.

16. (Original) The method of claim 15, wherein annealing is carried out at a temperature of at least 400°C.

17. (Original) The method of claim 15, wherein annealing is carried out in a non-oxidizing environment.

18. (Original) The method of claim 17, wherein the non-oxidizing environment is a reducing environment, containing a reducing gaseous component.

19. (Original) The method of claim 17, wherein the non-oxidizing environment comprises an non-reactive gas.

20. (Original) The method of claim 15, wherein the annealing is effective to reduce defects along a surface of the substrate.

21. (Original) The method of claim 15, wherein the annealing is effective to remove impurities along a surface of the substrate.

22. (Currently Amended) The method of claim 1, ~~further comprising a step of wherein~~ plasma treatment after cleaning is carried out at a pressure between  $10^{-2}$  to  $10^{-5}$  Torr.

23. (Currently Amended) The method of claim ~~[[22]]~~1, wherein the plasma treatment is effective to remove impurities along a surface of the substrate.

24. (Original) The method of claim 1, further comprising depositing a buffer layer overlying the substrate, prior to depositing the superconductor layer.

25. (Original) The method of claim 24, wherein the buffer layer includes at least one film that is biaxially textured.

26. (Original) The method of claim 25, wherein the biaxially textured layer film is formed by an IBAD process.

27. (Original) The method of claim 1, wherein the superconductor layer has a  $T_c$  not less than about 77K.

28. (Original) The method of claim 27, wherein the superconductor layer comprises YBCO.

29. (Original) The method of claim 1, further comprising depositing a stabilizer layer overlying the superconductor layer.

30. (Original) The method of claim 1, wherein the superconductive device is a superconductive tape.

31. (Original) The method of claim 1, wherein the superconductive device is an electric power component incorporating a superconductive tape comprising said substrate and superconductor layer.

32. (Original) The method of claim 1, wherein the substrate has first and second opposite major surfaces, at least the first opposite major surface being polycrystalline and randomly textured, the first opposite major surface being directly exposed to the cleaning medium during cleaning.

33. (Currently Amended) The method of claim ~~[[1]]~~32, wherein the superconductor layer overlies the first major surface.

Claims 34-38 (Canceled)

39. (New) The method of claim 1, wherein plasma treating is carried out while translating the substrate through a plasma chamber.

40. (New) A method of forming a superconductive device, comprising:  
polishing a substrate having a dimension ratio not less than  $10^2$ ;  
cleaning the substrate, cleaning including immersing the substrate in a fluid medium and  
subjecting the substrate to mechanical waves in the fluid medium;  
translating the substrate through a plasma chamber and into a deposition chamber;  
plasma treating the substrate while translating through the plasma chamber; and  
depositing at least one film of a buffer layer on the substrate while translating through the  
deposition chamber.